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**EVOLUTIONS OF GRAIN BOUNDARY RECOMBINATION ACTIVITY IN POLYCRYSTALLINE SILICON INVESTIGATED BY LBIC MAPPING AND DLTS**

M. PASQUINELLI, N. M'GAFFAD<sup>(1)</sup>, H. AMANRICH and S. MARTINUZZI

*Laboratoire de Photoélectricité des Semi-Conducteurs, Faculté des Sciences et Techniques de Marseille Saint-Jérôme, Université d'Aix-Marseille III, F-13397 Marseille Cedex 13, France*

In large grained polycrystalline silicon, the recombination activity of grain boundaries (G.B.'s) is typically heterogeneous. This activity may be evaluated by the determination of interfacial recombination velocity  $S$ ; which is related to the presence of deep trap levels at G.B.'s.

Photoconductance and LBIC mapping at  $\lambda = 940$  nm have been used to evaluate  $S$ , while D.L.T.S. measurements, applied to the space charge region of G.B.'s yield activation energy  $E_T$ , density  $N_T$  and capture cross section  $\sigma_T$  of associated centres.

In as-grown Polyx wafers,  $S$  is generally found in the range between  $10^3$ - $10^4$  cm.s<sup>-1</sup> and deep trap levels are located within the mid gap.

Annealings in argon at temperatures around 700°C increase  $S$  and  $N_T$ , while  $E_T$  and  $\sigma_T$  remain generally constant. These results indicate that the increase of  $S$  is due to that of  $N_T$  only, and the nature of the recombination centre source is not changed.

To reduce the recombination activity of G.B.'s, annealings in hydrogen gas flow at 280°C during 2h have been used /1/. The comparison of the measured characteristic values shows that  $S$  decreases by one order of magnitude at least. D.L.T.S. indicate that  $N_T$  decreases, while  $E_T$  and  $\sigma_T$  are not affected by the treatment.

The preceding results could be explained assuming that hydrogen passivation is not extended to the entire G.B. area and that in the region in which hydrogen has penetrated, all the recombination centres can be passivated. This last evolution is reversible, as annealing the wafers in argon at 350°C during 2 hours is sufficient to reconstitute the initial value of  $S$ , suggesting that Si-H bonds are not formed.

Reference

/1/ H. AMZIL, Thèse d'Etat Marseille 1985.

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<sup>(1)</sup> on leave of the E.N.S. of Takaddoum-Rabat, Maroc